

isc Silicon NPN Power Transistor

2SD961

DESCRIPTION

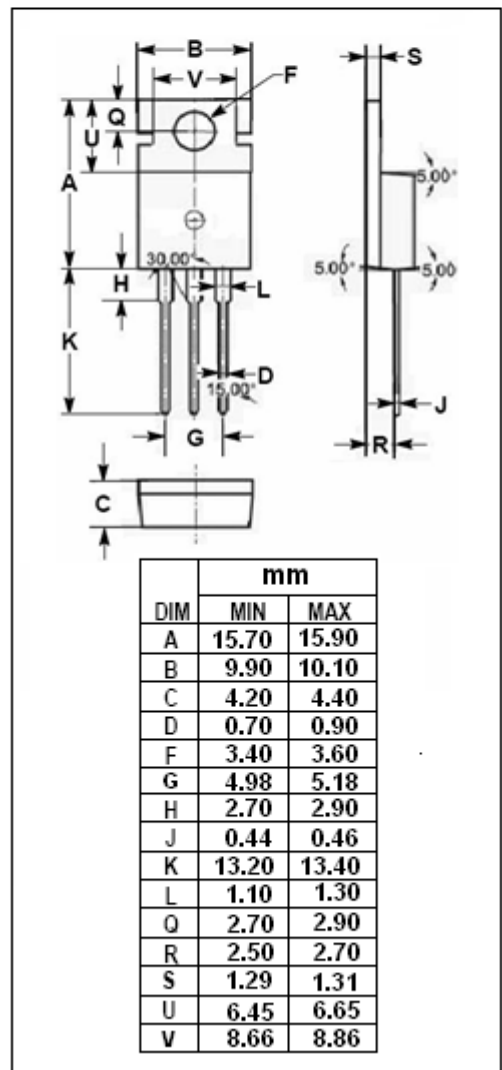
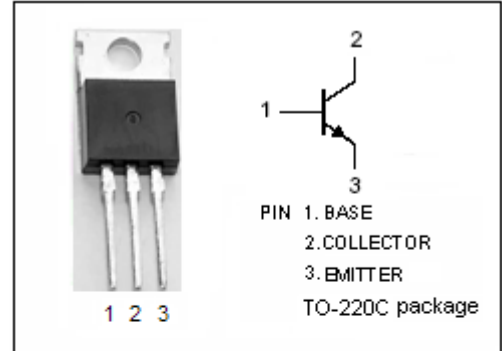
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 80V(\text{Min})$
- Good Linearity of h_{FE}
- Low Collector Saturation Voltage
: $V_{CE(sat)} = 0.5V(\text{Max}) @ I_C = 4A$
- Complement to Type 2SB869

APPLICATIONS

- Designed for power switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	130	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	10	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	40	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**2SD961****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.2\text{A}$			0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.2\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=100\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			50	μA
h_{FE-1}	DC Current Gain	$I_C=0.1\text{A}; V_{CE}=2\text{V}$	45			
h_{FE-2}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=2\text{V}$	60		260	
f_T	Current-Gain—Bandwidth Product	$I_C=0.5\text{A}; V_{CE}=10\text{V}$		30		MHz

Switching Times

t_{on}	Turn-On Time	$I_C=2\text{A}; I_{B1}=-I_{B2}=0.2\text{A}$		0.5		μs
t_s	Storage Time			1.5		μs
t_f	Fall Time			0.15		μs

◆ **h_{FE-2} Classifications**

R	Q	P
60-120	90-180	130-260